

4AK23

Silicon N-Channel Power MOS FET Array

HITACHI

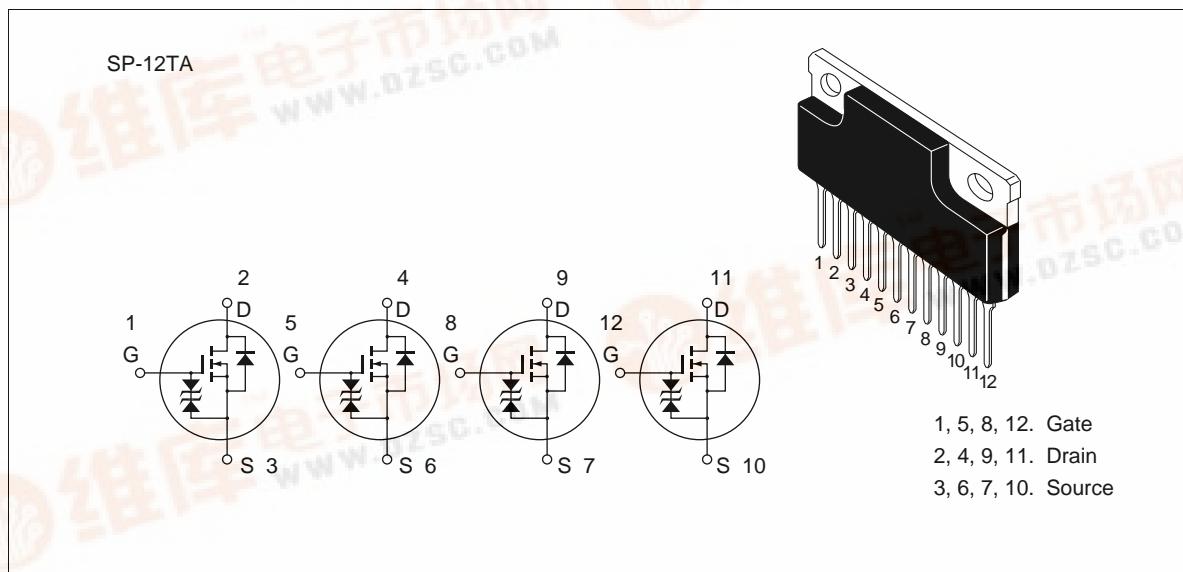
Application

High speed power switching

Features

- Low on-resistance
 $R_{DS(on)}$ 0.25 , $V_{GS} = 10$ V, $I_D = 2.5$ A
- Low drive current
- High speed switching
- High density mounting
- Suitable for H-bridged motor driver

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	5	A
Drain peak current	I _{D(pulse)} ^{*1}	20	A
Body to drain diode reverse drain current	I _{DR}	5	A
Channel dissipation	Pch (Tc = 25°C) ^{*2}	32	W
Channel dissipation	Pch ^{*2}	4	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. 4 Devices operation

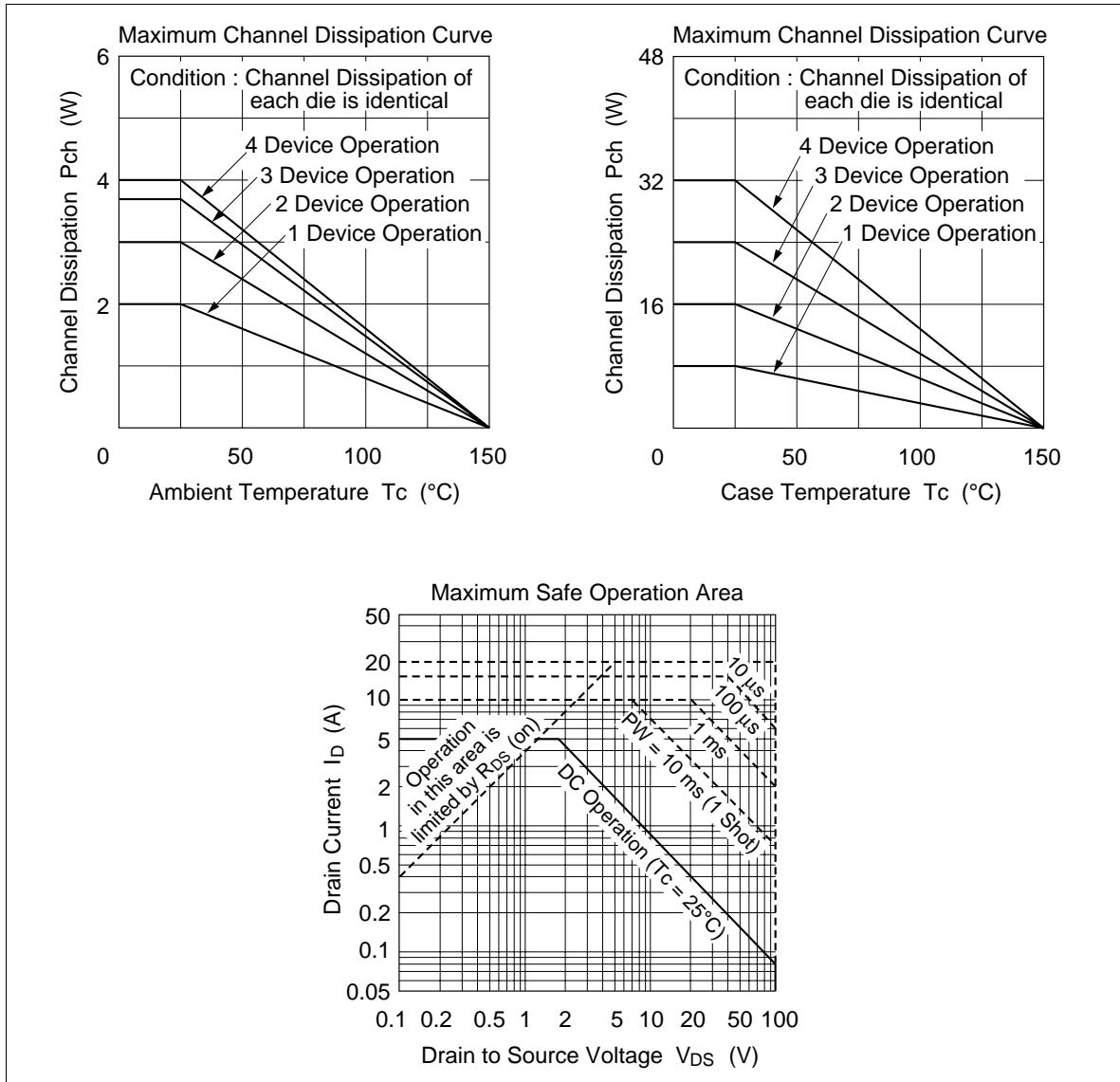
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 80 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.2	0.25	Ω	$I_D = 2.5 \text{ A}$ $V_{GS} = 10 \text{ V}^{\ast 1}$
		—	0.25	0.35	Ω	$I_D = 2.5 \text{ A}$ $V_{GS} = 4 \text{ V}^{\ast 1}$
Forward transfer admittance	$ y_{fs} $	3	5	—	S	$I_D = 2.5 \text{ A}$ $V_{DS} = 10 \text{ V}^{\ast 1}$
Input capacitance	C_{iss}	—	525	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	205	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	60	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	5	—	ns	$I_D = 2.5 \text{ A}$
Rise time	t_r	—	30	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	180	—	ns	$R_L = 12 \Omega$
Fall time	t_f	—	65	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	170	—	μs	$I_F = 5 \text{ A}, V_{GS} = 0,$ $dI/dt = 50 \text{ A}/\mu\text{s}$

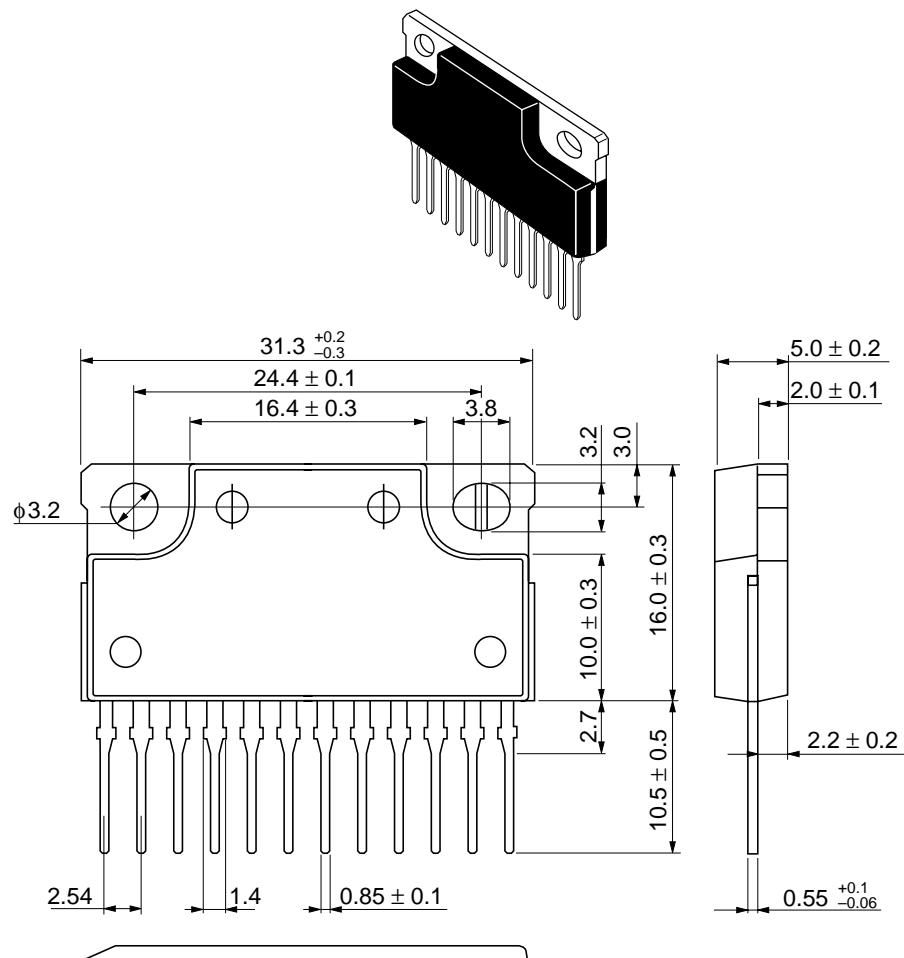
Note: 1. Pulse Test

See characteristic curves of 2SK1300

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Unit: mm



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